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ON Semiconductor®

FGH60N60UFDTU-F085

600V, 60A Field Stop IGBT

Features

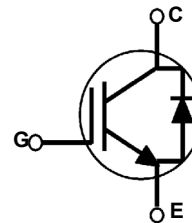
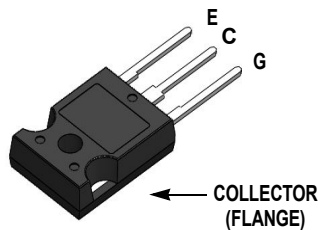
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.8\text{ V @ } I_C = 60\text{ A}$
- High Input Impedance
- Fast Switching
- RoHS Compliant
- Qualified to Automotive Requirements of AEC-Q101

Applications

- Automotive chargers, Converters, High Voltage Auxiliaries
- Inverters, PFC, UPS

General Description

Using Novel Field Stop IGBT Technology, ON Semiconductor's new series of Field Stop IGBTs offer the optimum performance for Auto-motive Chargers, Inverter, and other applications where low con-duction and switching losses are essential.



Absolute Maximum Ratings

Symbol	Description	Ratings	Unit
V_{CES}	Collector to Emitter Voltage	600	V
V_{GES}	Gate to Emitter Voltage	± 20	V
	Transient Gate-to-Emitter Voltage	± 30	
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	120	A
	Collector Current @ $T_C = 100^\circ\text{C}$	60	A
$I_{CM(1)}$	Pulsed Collector Current @ $T_C = 25^\circ\text{C}$	180	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	298	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	119	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Notes:

1: Repetitive test , Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Unit
$R_{\theta JC}(\text{IGBT})$	Thermal Resistance, Junction to Case	0.33	$^\circ\text{C/W}$
$R_{\theta JC}(\text{Diode})$	Thermal Resistance, Junction to Case	1.1	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	40	$^\circ\text{C/W}$

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGH60N60UFDU-F085	FGH60N60UFD	TO-247	Tube	N/A	N/A	30

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{CES}	Collector to Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 250\ \mu\text{A}$	600	-	-	V
$\Delta BV_{CES} / \Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 250\ \mu\text{A}$	-	0.67	-	V/°C
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	-	-	250	μA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	-	-	±400	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 250\ \mu\text{A}, V_{CE} = V_{GE}$	4.0	5.0	6.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 60\text{ A}, V_{GE} = 15\text{ V}$	-	1.8	2.9	V
		$I_C = 60\text{ A}, V_{GE} = 15\text{ V}, T_C = 125^\circ\text{C}$	-	2.1	-	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	-	2540	-	pF
C_{oes}	Output Capacitance		-	330	-	pF
C_{res}	Reverse Transfer Capacitance		-	110	-	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}, I_C = 60\text{ A}, R_G = 5\ \Omega, V_{GE} = 15\text{ V}, \text{Inductive Load}, T_C = 25^\circ\text{C}$	-	29	-	ns
t_r	Rise Time		-	60	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	138	-	ns
t_f	Fall Time		-	28	80	ns
E_{on}	Turn-On Switching Loss		-	2.47	-	mJ
E_{off}	Turn-Off Switching Loss		-	0.81	-	mJ
E_{ts}	Total Switching Loss		-	3.28	-	mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}, I_C = 60\text{ A}, R_G = 5\ \Omega, V_{GE} = 15\text{ V}, \text{Inductive Load}, T_C = 125^\circ\text{C}$	-	28	-	ns
t_r	Rise Time		-	55	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	147	-	ns
t_f	Fall Time		-	71	-	ns
E_{on}	Turn-On Switching Loss		-	3.01	-	mJ
E_{off}	Turn-Off Switching Loss		-	1.21	-	mJ
E_{ts}	Total Switching Loss		-	4.22	-	mJ
Q_g	Total Gate Charge	$V_{CE} = 400\text{ V}, I_C = 60\text{ A}, V_{GE} = 15\text{ V}$	-	192	-	nC
Q_{ge}	Gate to Emitter Charge		-	24	-	nC
Q_{gc}	Gate to Collector Charge		-	102	-	nC

Electrical Characteristics of the Diode T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max	Units	
V _{FM}	Diode Forward Voltage	I _F = 30 A	T _C = 25°C	-	1.70	2.6	V
			T _C = 125°C	-	1.54	-	
t _{rr}	Diode Reverse Recovery Time	I _F = 30 A, di _F /dt = 200 A/μs	T _C = 25°C	-	76	-	ns
			T _C = 125°C	-	242	-	
Q _{rr}	Diode Reverse Recovery Charge	I _F = 30 A, di _F /dt = 200 A/μs	T _C = 25°C	-	208	-	nC
			T _C = 125°C	-	1162	-	

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

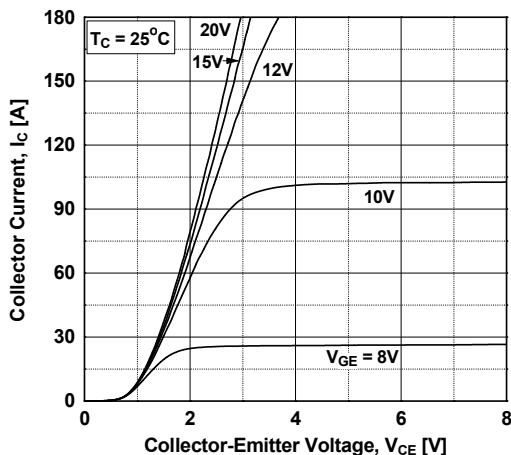


Figure 2. Typical Output Characteristics

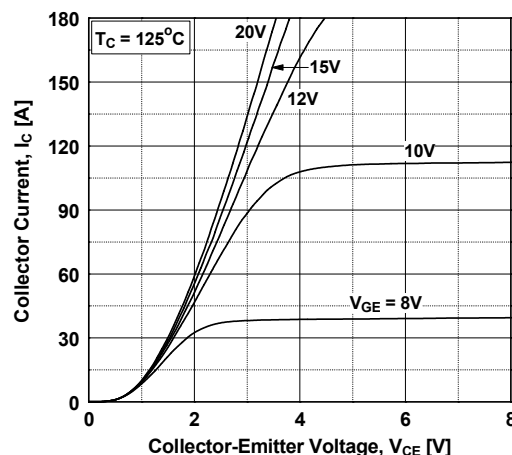


Figure 3. Typical Saturation Voltage Characteristics

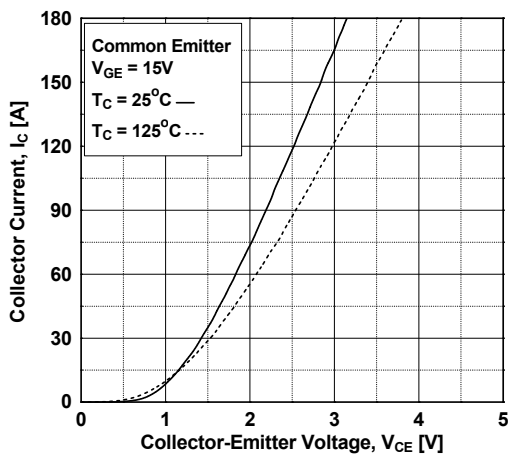


Figure 4. Transfer Characteristics

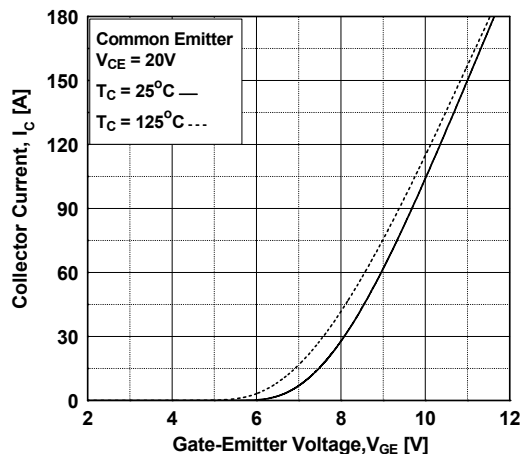


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

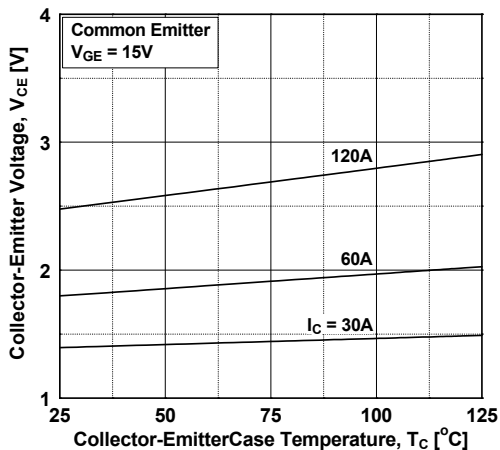
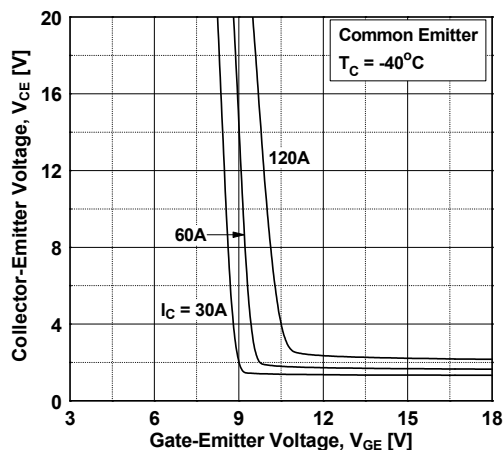


Figure 6. Saturation Voltage vs. Vge



Typical Performance Characteristics

Figure 7. Saturation Voltage vs. V_{GE}

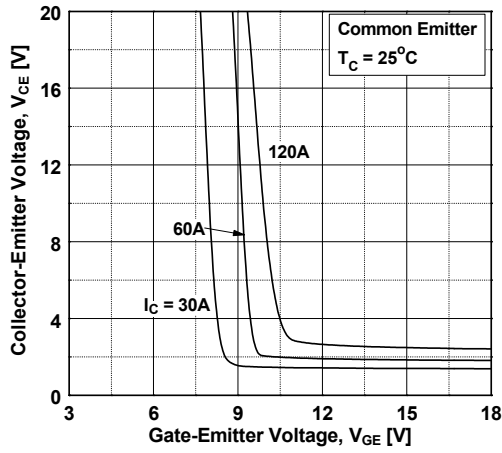


Figure 8. Saturation Voltage vs. V_{GE}

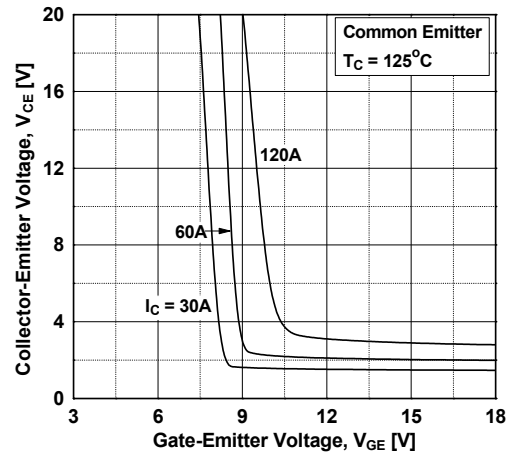


Figure 9. Capacitance Characteristics

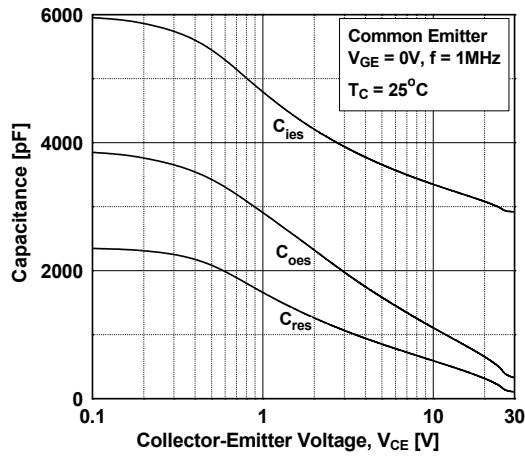


Figure 10. Gate charge Characteristics

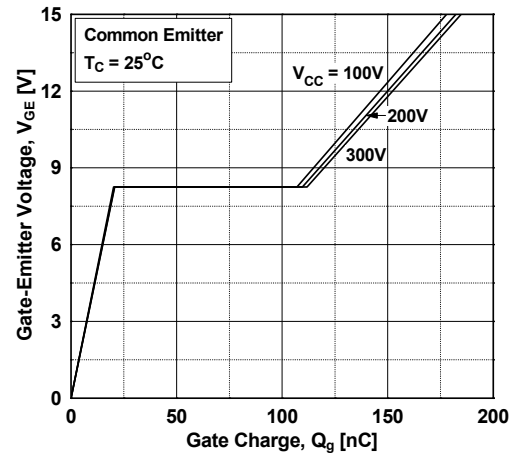


Figure 11. SOA Characteristics

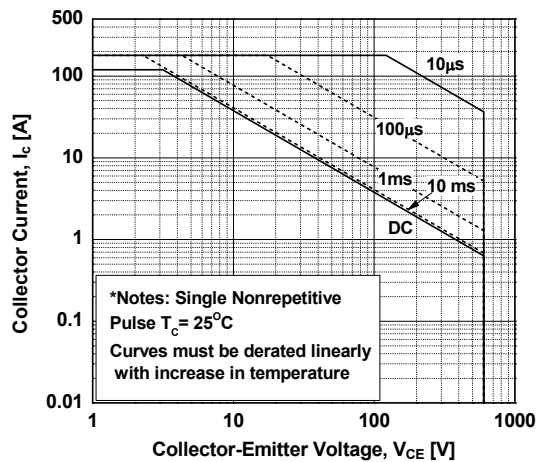
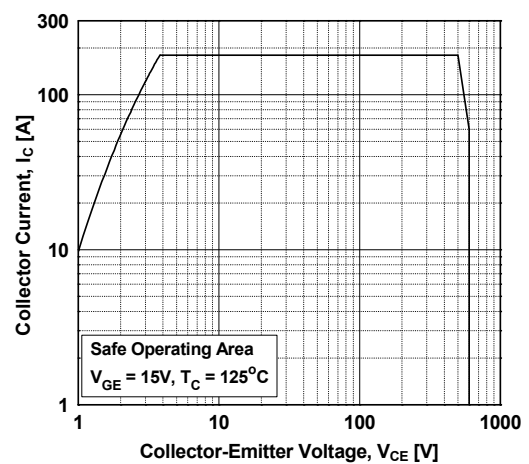


Figure 12. Turn off Switching SOA



Typical Performance Characteristics

Figure 13. Turn-on Characteristics vs. Gate Resistance

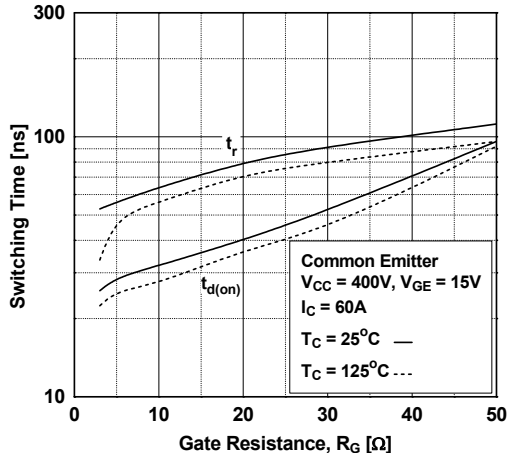


Figure 14. Turn-off Characteristics vs. Gate Resistance

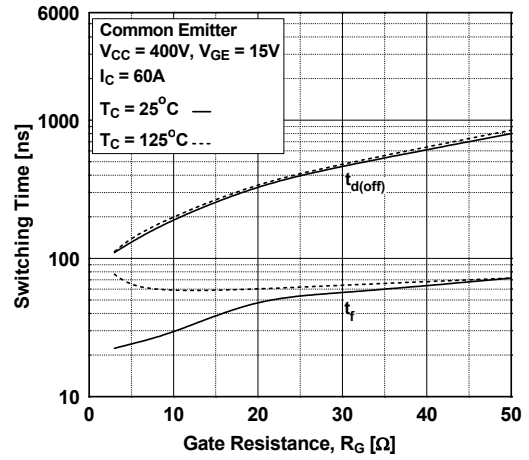


Figure 15. Turn-on Characteristics vs. Collector Current

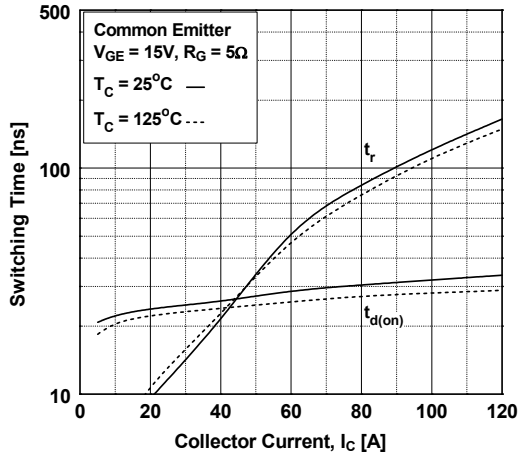


Figure 16. Turn-off Characteristics vs. Collector Current

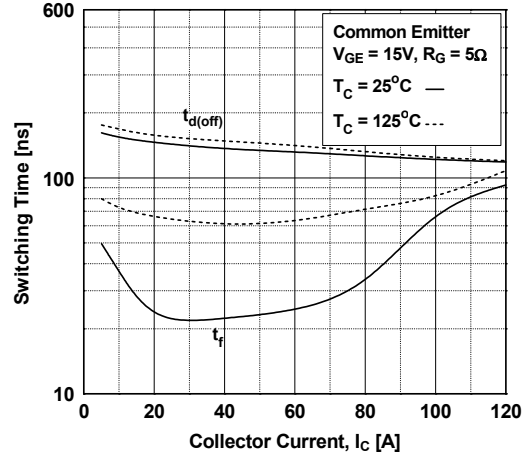


Figure 17. Switching Loss vs. Gate Resistance

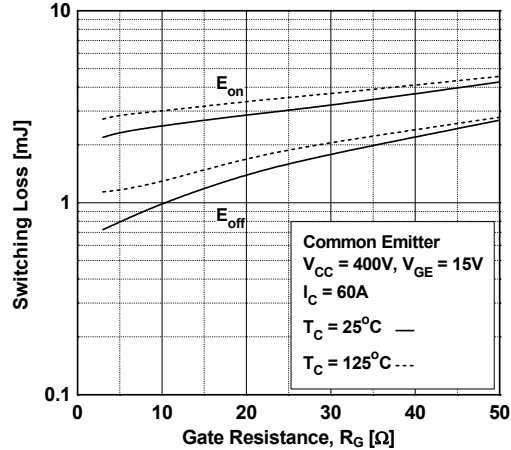
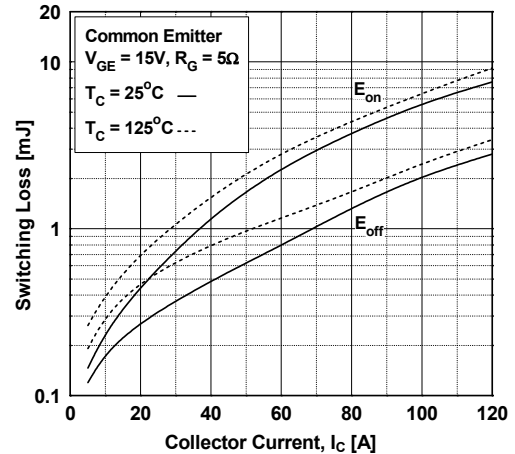


Figure 18. Switching Loss vs. Collector Current



Typical Performance Characteristics

Figure 19. Forward Characteristics

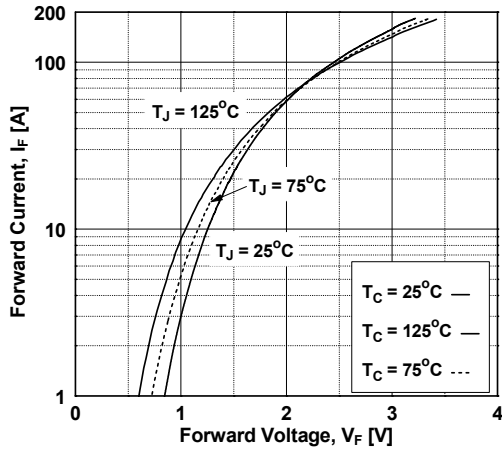


Figure 20. Reverse Current

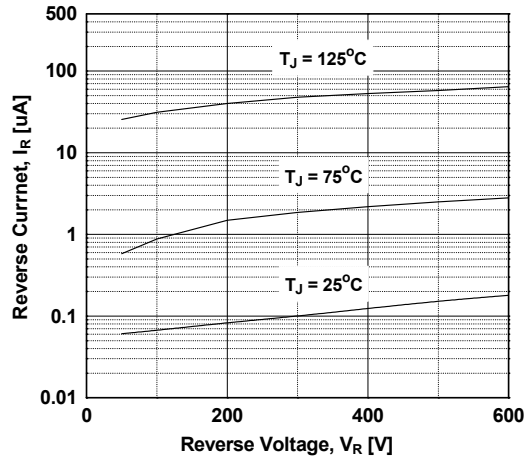


Figure 21. Stored Charge

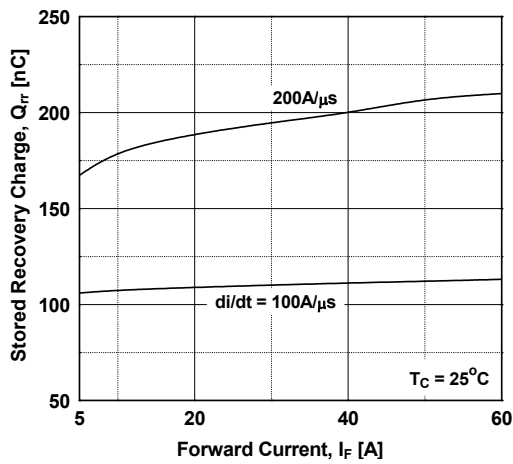


Figure 22. Reverse Recovery Time

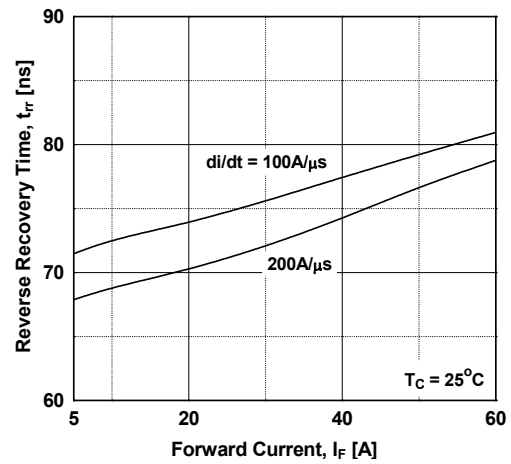
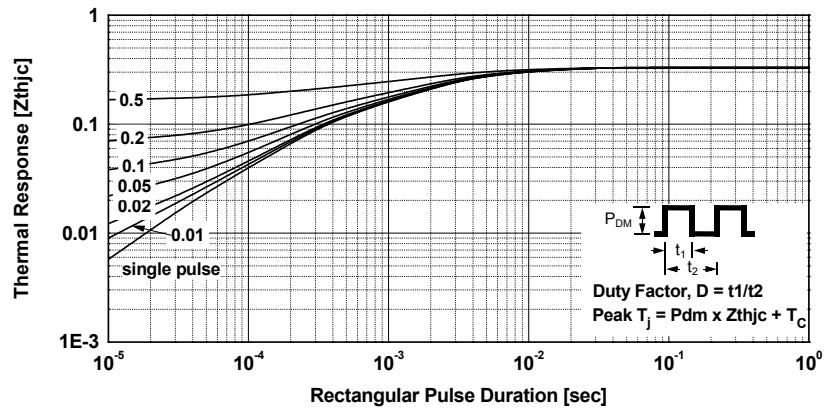
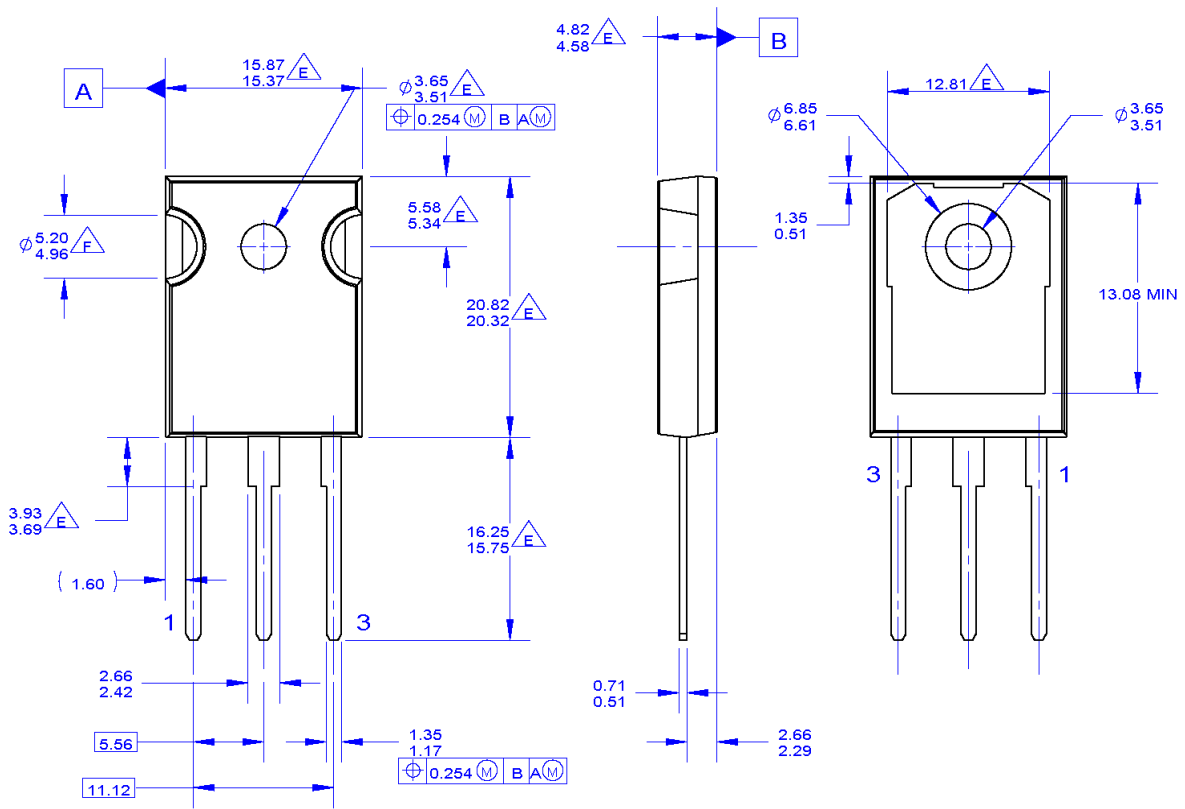


Figure 23. Transient Thermal Impedance of IGBT



Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED.

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- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5 - 1994

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Figure 24. TO-247 3L - TO-247,MOLDED,3 LEAD,JEDEC VARIATION AB

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